

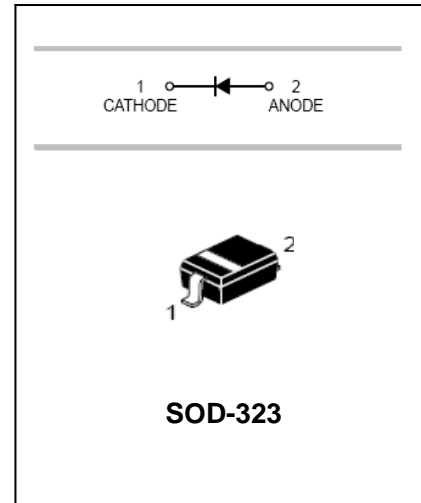
Silicon Epitaxial Planar Diode

1N4148WS
FEATURES

- Fast Switching Speed: $t_{rr}=4ns$ (Typ)
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance
- Available in Lead Free Version



Lead-free


APPLICATIONS

- Surface mount fast switching diode

ORDERING INFORMATION

Type No.	Marking	Package Code
1N4148WS	T4	SOD-323

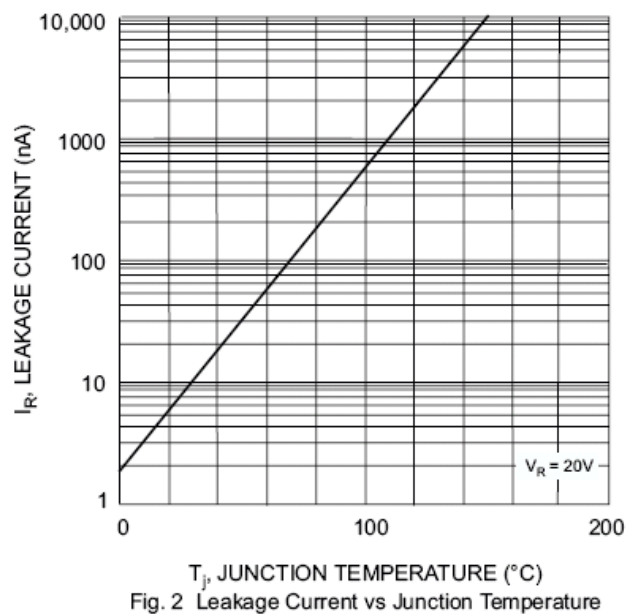
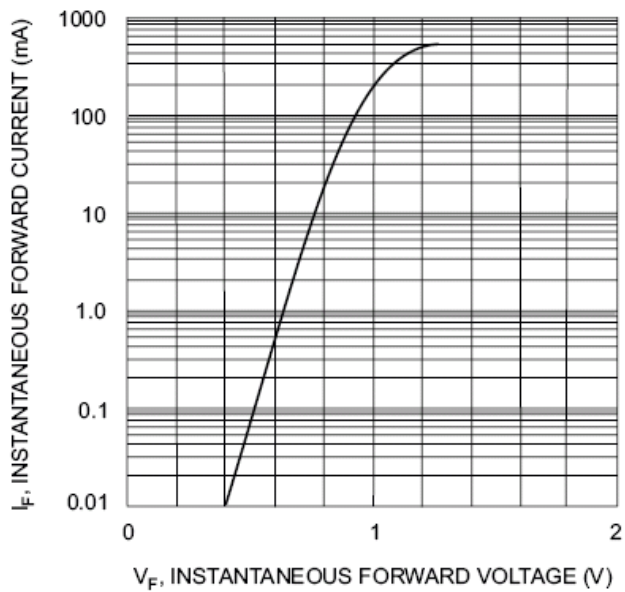
MAXIMUM RATING @ $T_a=25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_o	150	mA
Non-Repetitive Peak Forward Surge Current @ $t=1.0 \mu s$	I_{FSM}	2.0	A
@ $t=1.0 s$		1.0	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ C/W$
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ C$

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ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V	$I_R=1.0\mu\text{A}$
Forward Voltage	V_F	-	0.715 0.855 1.0 1.25	V	$I_F=1.0\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$
Reverse Current	I_R	-	1.0 25	μA nA	$V_R=75\text{V}$ $V_R=20\text{V}$
Capacitance between terminals	C_T	-	2.0	pF	$V_R=0, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	-	4.0	ns	$I_F=I_R=10\text{mA}$, $I_{rr}=0.1 \times I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified


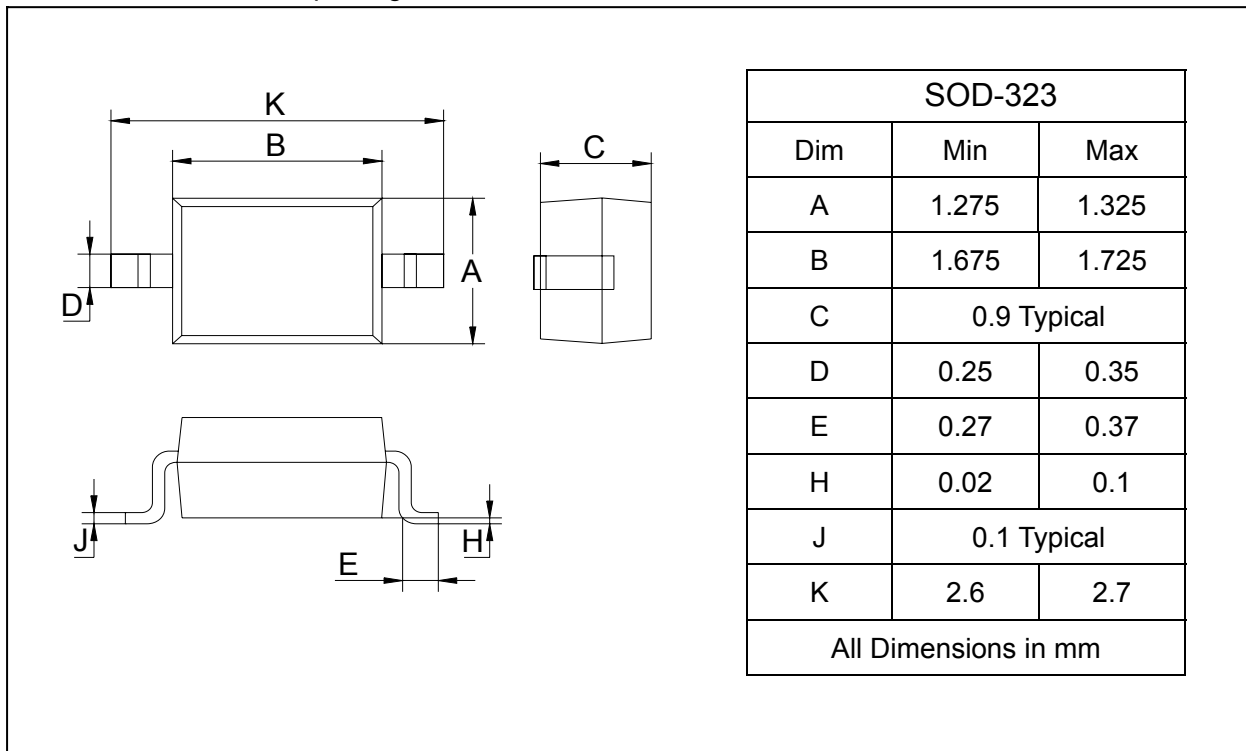
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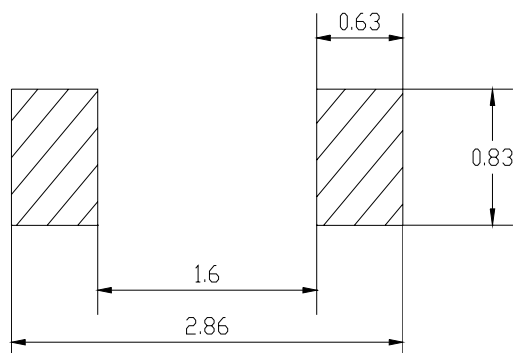
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
1N4148WS	SOD-323	3000/Tape&Reel